Dual N-Channel Enhancement-Mode Vertical DMOS FET

Features

- Dual N-channel devices
- Low threshold – 2.0V max.
- High input impedance
- Low input capacitance – 125pF max.
- Fast switching speeds
- Low on-resistance
- Free from secondary breakdown
- Low input and output leakage

Applications

- Logic level interfaces – ideal for TTL and CMOS
- Solid state relays
- Battery operated systems
- Photo voltaic drives
- Analog switches
- General purpose line drivers
- Telecom switches

General Description

This low threshold, enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven, silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Part Number	Package Option	Packing
TD9944TG-G	8-Lead SOIC	2000/Reel

-G denotes a lead (Pb)-free / RoHS compliant package.

Product Summary

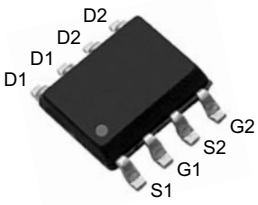
BV_{DSS}/BV_{DGS}	$R_{DS(ON)}$ (max)	$I_{D(ON)}$ (min)	$V_{GS(th)}$ (max)
240V	6.0Ω	1.0A	2.0V

Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV_{DSS}
Drain-to-gate voltage	BV_{DGS}
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Pin Configuration



8-Lead SOIC

Typical Thermal Resistance

Package	θ_{ja}
TO-243AA (SOT-89)	133°C/W

Note:
Mounted on FR5 Board, 25mm x 25mm x 1.57mm

Product Marking

YY = Year Sealed
WW = Week Sealed
———— = "Green" Packaging

Package may or may not include the following marks: Si or

8-Lead SOIC

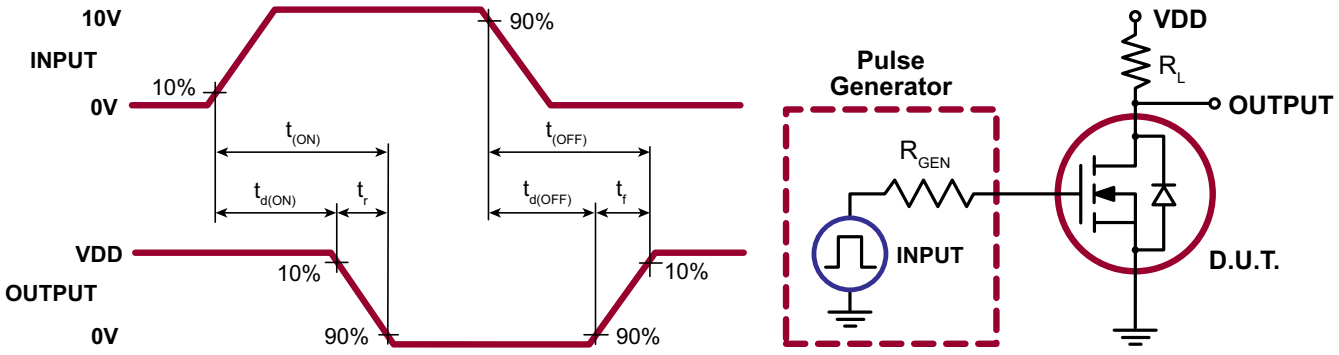
Electrical Characteristics (T_A = 25°C unless otherwise specified)

Sym	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSS}	Drain-to-source breakdown voltage	240	-	-	V	V_{GS} = 0V, I_D = 2.0mA
$V_{GS(th)}$	Gate threshold voltage	0.6	-	2.0	V	V_{GS} = V_{DS}, I_D= 1.0mA
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	-	-5.0	mV/°C	V_{GS} = V_{DS}, I_D= 1.0mA
I_{GSS}	Gate body leakage	-	-	100	nA	V_{GS} = ± 20V, V_{DS} = 0V
I_{DSS}	Zero gate voltage drain current	-	-	10	µA	V_{GS} = 0V, V_{DS} = Max Rating
		-	-	1.0	mA	V_{DS} = 0.8Max Rating, V_{GS} = 0V, T_A = 125°C
$I_{D(ON)}$	ON-state drain current	0.5	1.9	-	A	V_{GS} = 4.5V, V_{DS} = 25V
		1.0	2.8	-		V_{GS} = 10V, V_{DS} = 25V
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	4.0	6.0	Ω	V_{GS} = 4.5V, I_D = 250mA
		-	4.0	6.0		V_{GS} = 10V, I_D = 0.5A
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	-	1.4	%/°C	V_{GS} = 10V, I_D = 0.5A
G_{FS}	Forward transductance	300	600	-	mmho	V_{DS} = 20V, I_D = 0.5A
C_{ISS}	Input capacitance	-	65	125	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0MHz
C_{OSS}	Common source output capacitance	-	35	70		
C_{RSS}	Reverse transfer capacitance	-	10	25		
$t_{d(ON)}$	Turn-on delay time	-	-	10	ns	V_{DD} = 25V, I_D = 1.0A, R_{GEN} = 25Ω
t_r	Rise time	-	-	10		
$t_{d(OFF)}$	Turn-off delay time	-	-	20		
t_f	Fall time	-	-	20		
V_{SD}	Diode forward voltage drop	-	-	1.8	V	V_{GS} = 0V, I_{SD} = 1.0A
t_{rr}	Reverse recovery time	-	300	-	ns	V_{GS} = 0V, I_{SD} = 1.0A

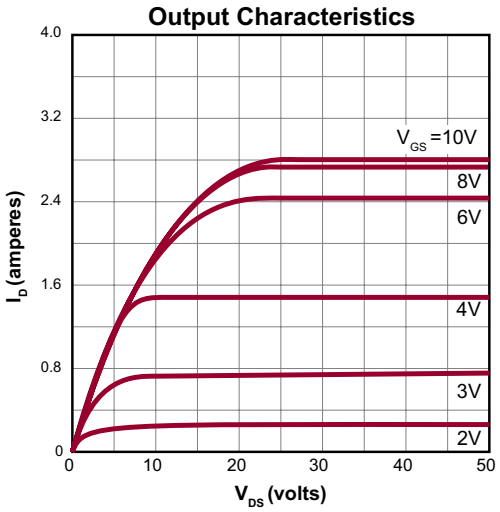
Notes:

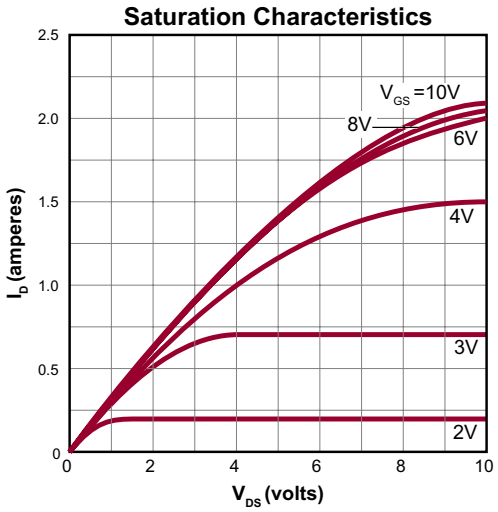
1. *All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)*
2. *All A.C. parameters sample tested.*

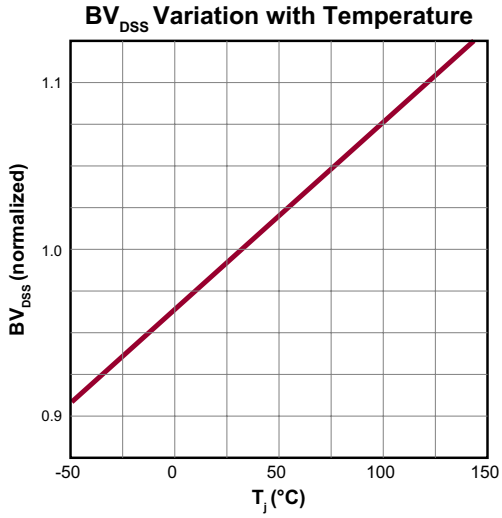
Switching Waveforms and Test Circuit

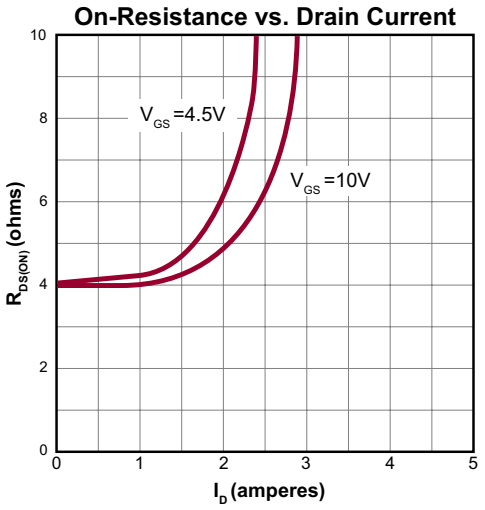


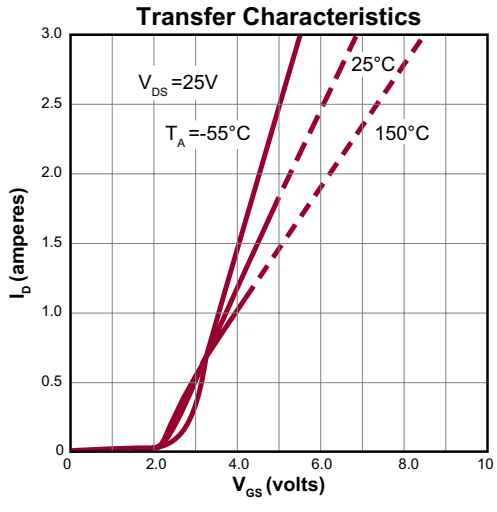
Typical Performance Curves

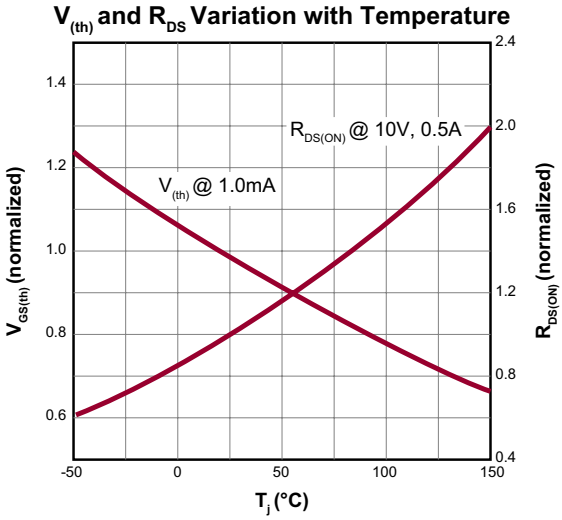




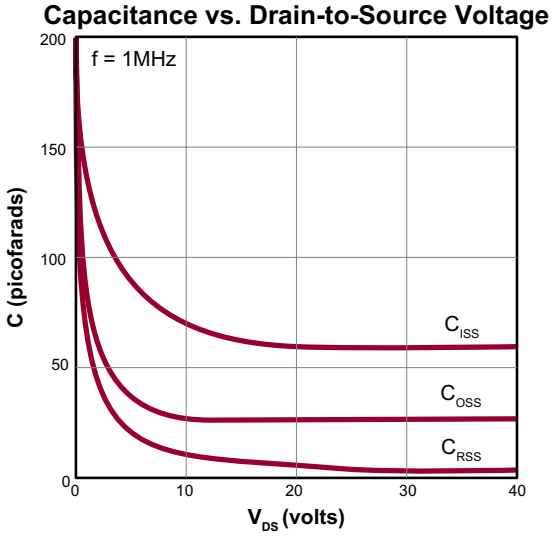


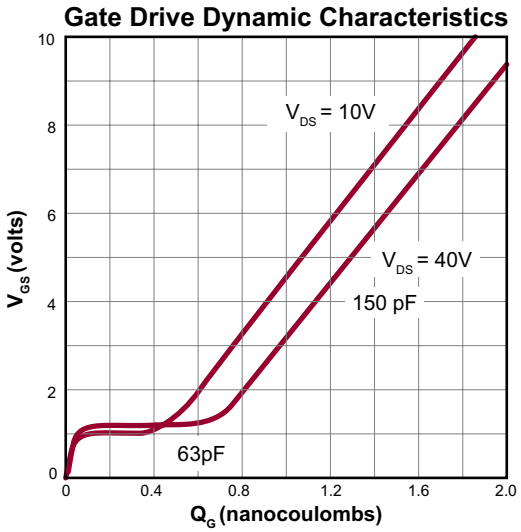


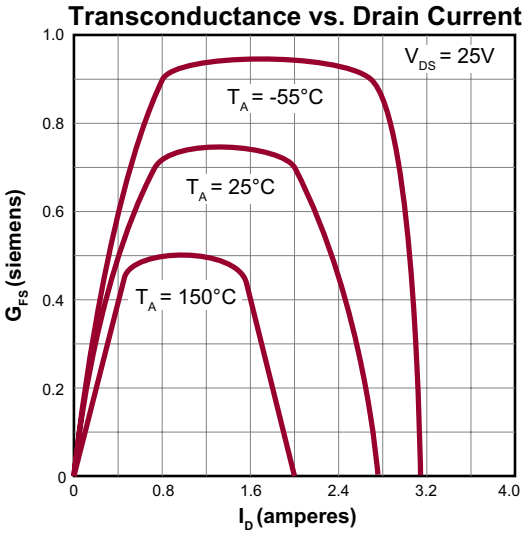




Typical Performance Curves *(cont.)*

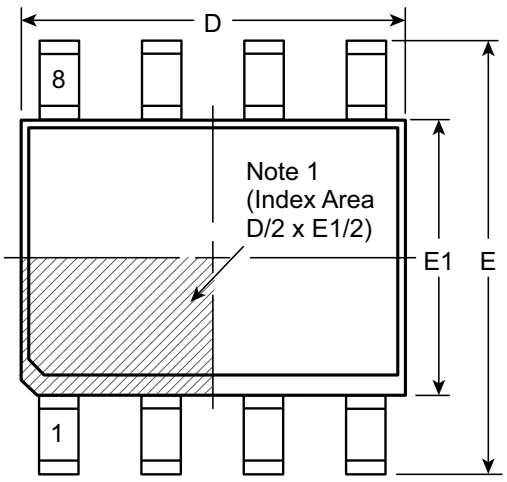




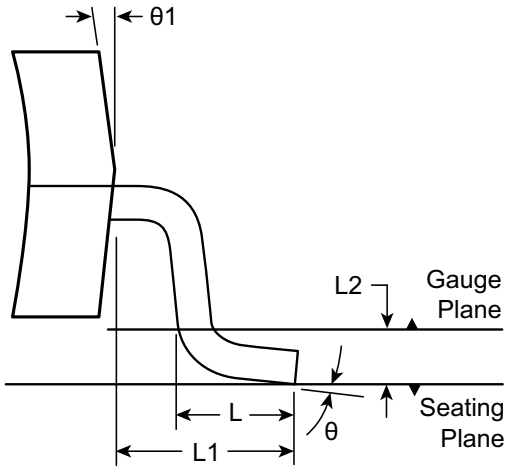


8-Lead SOIC (Narrow Body) Package Outline (TG)

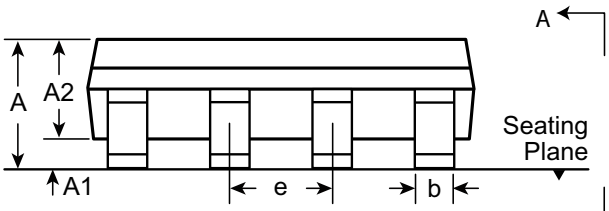
4.90x3.90mm body, 1.75mm height (max), 1.27mm pitch



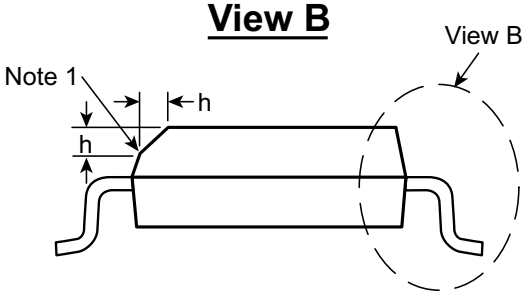
Top View



View B



Side View



View A-A

Note:

1. *This chamfer feature is optional. A Pin 1 identifier must be located in the index area indicated. The Pin 1 identifier can be: a molded mark/identifier; an embedded metal marker; or a printed indicator.*

Symbol		A	A1	A2	b	D	E	E1	e	h	L	L1	L2	θ	θ1
Dimension (mm)	MIN	1.35*	0.10	1.25	0.31	4.80*	5.80*	3.80*	1.27 BSC	0.25	0.40	1.04 REF	0.25 BSC	0°	5°
	NOM	-	-	-	-	4.90	6.00	3.90		-	-			-	-
	MAX	1.75	0.25	1.65*	0.51	5.00*	6.20*	4.00*		0.50	1.27			8°	15°

JEDEC Registration MS-012, Variation AA, Issue E, Sept. 2005.
** This dimension is not specified in the JEDEC drawing.*
Drawings are not to scale.
***Supertex Doc. #:** DSPD-8SOLGTG, Version I041309.*

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

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